

MOS FIELD EFFECT TRANSISTOR μ PA2727UT1A

SWITCHING N-CHANNEL POWER MOSFET

DESCRIPTION

The μ PA2727UT1A is N-channel MOSFET designed for DC/DC converter applications.

FEATURES

• Low on-state resistance

 $R_{DS(on)1}$ = 9.6 m Ω MAX. (V_{GS} = 10 V, I_D = 8 A)

 $R_{DS(on)2}$ = 15 $m\Omega$ MAX. (Vgs = 4.5 V, ID = 8 A)

• Low QgD

 $Q_{GD} = 3.5 \text{ nC TYP.}$ ($V_{DD} = 15 \text{ V}$, $I_{D} = 16 \text{ A}$)

- Thin type surface mount package with heat spreader (8-pin HVSON)
- RoHS Compliant

ABSOLUTE MAXIMUM RATINGS (TA = 25°C, All terminals are connected.)

VDSS	30	V
Vgss	±20	V
ID(DC)	±16	Α
I _{D(pulse)}	±96	Α
P _{T1}	1.5	W
P _{T2}	4.6	W
Tch	150	°C
Tstg	-55 to +150	°C
las	16	Α
Eas	26	mJ
	VGSS ID(DC) ID(pulse) PT1 PT2 Tch Tstg IAS	VGSS ±20 ID(DC) ±16 ID(pulse) ±96 PT1 1.5 PT2 4.6 Tch 150 Tstg -55 to +150 IAS 16

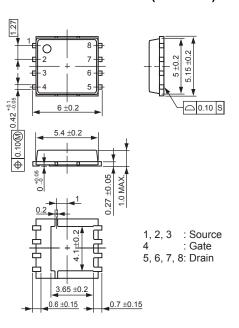
THERMAL RESISTANCE

Channel to Ambient Thermal Resistance Note2	Rth(ch-A)	83.3	°C/W
Channel to Case (Drain) Thermal Resistance	Rth(ch-C)	2.0	°C/W

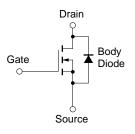
Notes 1. PW \leq 10 μ s, Duty Cycle \leq 1%

- 2. Mounted on a glass epoxy board of 25.4 mm x 25.4 mm x 0.8 mm
- 3. Starting T_{ch} = 25°C, V_{DD} = 15 V, R_G = 25 Ω , V_{GS} = 20 \rightarrow 0 V, L = 100 μ H

PACKAGE DRAWING (Unit: mm)



EQUIVALENT CIRCUIT



Remark Strong electric field, when exposed to this device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it once, when it has occurred.

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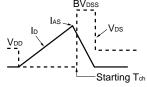
ELECTRICAL CHARACTERISTICS (TA = 25°C, All terminals are connected.)

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CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	IDSS	V _{DS} = 30 V, V _{GS} = 0 V			10	μΑ
Gate Leakage Current	Igss	V _{GS} = ±20 V, V _{DS} = 0 V			±100	nA
Gate to Source Cut-off Voltage	V _{GS(off)}	V _{DS} = 10 V, I _D = 1 mA			2.5	V
Forward Transfer Admittance Note	y fs	V _{DS} = 10 V, I _D = 8 A	6			S
Drain to Source On-state Resistance Note	RDS(on)1	V _{GS} = 10 V, I _D = 8 A		7.6	9.6	mΩ
	R _{DS(on)2}	V _{GS} = 4.5 V, I _D = 8 A		11	15	mΩ
Input Capacitance	Ciss	V _{DS} = 15 V,		1170		pF
Output Capacitance	Coss	V _{GS} = 0 V,		250		pF
Reverse Transfer Capacitance	Crss	f = 1 MHz		90		pF
Turn-on Delay Time	t _{d(on)}	V _{DD} = 15 V, I _D = 8 A,		13		ns
Rise Time	tr	V _{GS} = 10 V,		3.6		ns
Turn-off Delay Time	t _{d(off)}	R _G = 10 Ω		41		ns
Fall Time	t f			8		ns
Total Gate Charge	Q _G	V _{DD} = 15 V,		11		nC
Gate to Source Charge	Qgs	V _{GS} = 5 V,		3.8		nC
Gate to Drain Charge	Q _{GD}	I _D = 16 A		3.5		nC
Body Diode Forward Voltage Note	V _{F(S-D)}	I _F = 16 A, V _{GS} = 0 V		0.83		V
Reverse Recovery Time	trr	I _F = 16 A, V _{GS} = 0 V,		27		ns
Reverse Recovery Charge	Qrr	di/dt = 100 A/μs		23		nC
Gate Resistance	R _G	f = 1 MHz		2.2		Ω

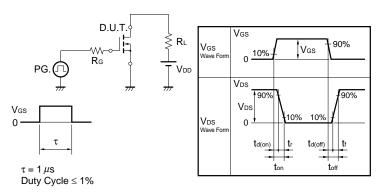
Note Pulsed

TEST CIRCUIT 1 AVALANCHE CAPABILITY

$V_{GS} = 20 \rightarrow 0 \text{ V}$ $PG. \bigcirc PG. \bigcirc PG.$



TEST CIRCUIT 2 SWITCHING TIME



TEST CIRCUIT 3 GATE CHARGE

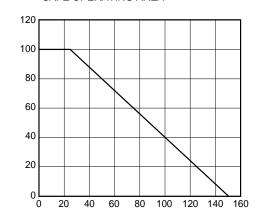
$$\begin{array}{c|c} D.U.T. \\ I_G = 2 \begin{array}{c} mA \\ \hline \end{array} \\ \hline \end{array}$$

dT - Percentage of Rated Power - %

Ip - Drain Current - A

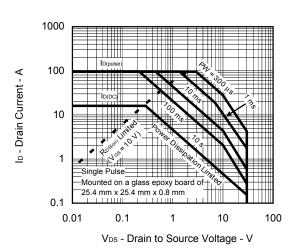
TYPICAL CHARACTERISTICS (TA = 25°C)

DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA

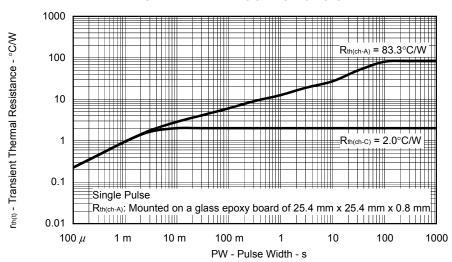


T_A - Ambient Temperature - °C

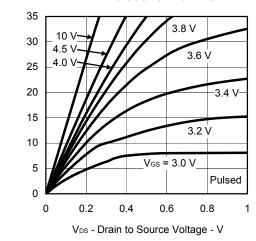
FORWARD BIAS SAFE OPERATING AREA



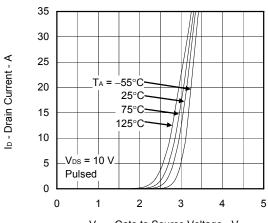
TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



DRAIN CURRENT vs.
DRAIN TO SOURCE VOLTAGE

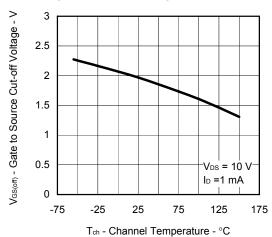


FORWARD TRANSFER CHARACTERISTICS

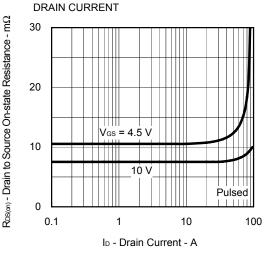


V_{GS} - Gate to Source Voltage - V

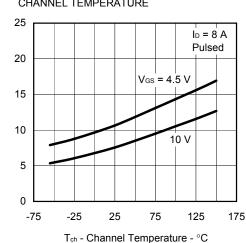
GATE TO SOURCE CUT-OFF VOLTAGE vs. CHANNEL TEMPERATURE



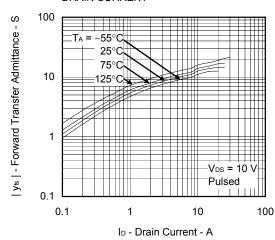
DRAIN TO SOURCE ON-STATE RESISTANCE vs.



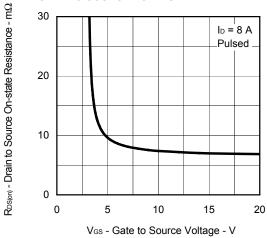
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



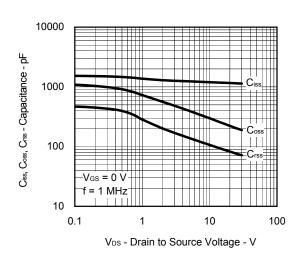
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE

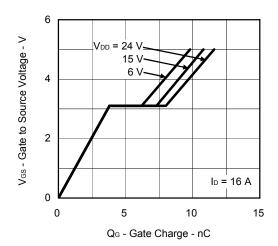


CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE

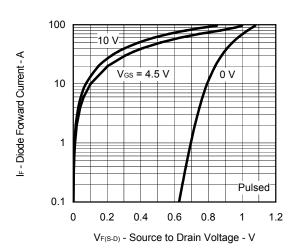


R_{DS(on)} - Drain to Source On-state Resistance - mΩ

DYNAMIC INPUT/OUTPUT CHARACTERISTICS



SOURCE TO DRAIN DIODE FORWARD VOLTAGE



ORDERING INFORMATION

PART NUMBER	LEAD PLATING	PACKING	PACKAGE	
μPA2727UT1A-E1-AZ Note	Co. Di			
μPA2727UT1A-E2-AZ Note	Sn-Bi	T 2000 -/I	8-pin HVSON	
μPA2727UT1A-E1-AY Note	D 0	Tape 3000 p/reel	0.10 g TYP.	
μPA2727UT1A-E2-AY Note	Pure Sn			

Note Pb-free (This product does not contain Pb in the external electrode.)

 μ PA2727UT1A

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